L Number	Hits	Search Text	DB	Time stamp
38	5141	semiconductor near laser near diode	USPAT;	2003/07/27 12:53
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
39	28	(semiconductor near laser near diode) and passive\$3 near3	USPAT;	2003/07/27 13:14
		mode near3 lock\$3	US-PGPUB;	
			EPO; JPO;	
			DERWENT	
40	23	((semiconductor near laser near diode) and passive\$3 near3	USPAT;	2003/07/27 12:55
		mode near3 lock\$3) and method	US-PGPUB;	
			EPO; JPO;	
}			DERWENT	
41	17	(semiconductor near laser near diode) and passive\$3 near3	USPAT;	2003/07/27 13:14
		resonator	US-PGPUB;	
1			EPO; JPO;	
		l	DERWENT	
42	6	((semiconductor near laser near diode) and passive\$3 near3	USPAT;	2003/07/27 13:25
		resonator) and mode near3 lock\$3	US-PGPUB;	
			EPO; JPO;	
			DERWENT	
44	8	((passive near3 resonat\$3) and mode near3 lock\$3) and (align\$4	USPAT;	2003/07/27 13:32
		or misalign\$4)	US-PGPUB;	
			EPO; JPO;	
		l	DERWENT	
45	6	((passive near3 resonat\$3) and mode near3 lock\$3) and mirror\$1	USPAT;	2003/07/27 13:33
		near3 (adjust\$4 or rotat\$4)	US-PGPUB;	•
			EPO; JPO;	
			DERWENT	0000/07/07 40 40
46	1		USPAT	2003/07/27 13:43
47	1		USPAT	2003/07/27 13:44
48	1		USPAT	2003/07/27 13:44
49	1		USPAT	2003/07/27 13:44
50	1		USPAT	2003/07/27 13:45
51	_1		USPAT	2003/07/27 13:45
43	33	(passive near3 resonat\$3) and mode near3 lock\$3	USPAT;	2003/07/27 14:02
			US-PGPUB;	
			EPO; JPO;	
	050		DERWENT	0000/07/07 40 50
52	252	semiconductor near3 ring near3 laser	USPAT;	2003/07/27 13:53
			US-PGPUB;	
			EPO; JPO;	
50		(DERWENT	0000/07/07 40-55
53	4	(semiconductor near3 ring near3 laser) and (passive\$3 near3	USPAT;	2003/07/27 13:55
		mode near3 lock\$3)	US-PGPUB;	
			EPO; JPO;	
	4	//comiconductor near? rise mean? leases and meaning means	DERWENT	2002/07/27 42:55
55	1	((semiconductor near3 ring near3 laser) and passive near3	USPAT;	2003/07/27 13:55
		resonat\$3) and mode near3 lock\$3	US-PGPUB;	
			EPO; JPO;	
54	00	(comicondustor poor2 ring poor2 least) and necessity	DERWENT	2002/07/27 42:50
54	23	(semiconductor near3 ring near3 laser) and passive near3	USPAT;	2003/07/27 13:56
		resonat\$3	US-PGPUB;	
			EPO; JPO;	
	400	(naccing many) manual(0) === 1 (//	DERWENT	0000/07/07 44:00
56	102	(passive near3 resonat\$3) and ((frequency or mode) near3	USPAT;	2003/07/27 14:03
		lock\$3)	US-PGPUB;	
			EPO; JPO;	
57	400044	nomiconductor nearElectric	DERWENT	0000/07/07 44:04
	100011	semiconductor near5 laser	USPAT;	2003/07/27 14:04
			US-PGPUB;	
			EPO; JPO;	
_		//	DERWENT	0000107107111
58	36	((passive near3 resonat\$3) and ((frequency or mode) near3	USPAT;	2003/07/27 14:09
		lock\$3)) and semiconductor near5 laser	US-PGPUB;	
			EPO; JPO;	
		I	DERWENT	İ

59	5	"5383198"	USPAT;	2003/07/27 14:09
			US-PGPUB;	
			EPO; JPO;	
•		· · · · · · · · · · · · · · · · · · ·	DERWENT	
60	1	("5383198").PN.	USPAT;	2003/07/27 14:10
,			US-PGPUB	
61	31	(laser near3 diode) and ((frequency or mode) near3 lock\$3) and	USPAT;	2003/07/27 14:15
	İ	passive near3 resonat\$3	US-PGPUB;	
			EPO; JPO;	
			DERWENT	
62	19	((laser near3 diode) and ((frequency or mode) near3 lock\$3) and	USPAT;	2003/07/27 14:29
		passive near3 resonat\$3) and (align\$4 or misalign\$4 or	US-PGPUB;	
		realign\$4)	EPO; JPO;	
			DERWENT	0000/07/07 44:04
63	6	(semiconductor near3 laser near3 diode) and (passive near3	USPAT;	2003/07/27 14:34
		resonator) and (mode near3 lock\$3)	US-PGPUB;	
			EPO; JPO;	
			DERWENT	0000/07/07 44:05
64	1	(semiconductor near3 laser near3 diode) and (passive near3	USPAT;	2003/07/27 14:35
		resonator) and (self near3 mode near3 lock\$3)	US-PGPUB;	
			EPO; JPO;	
0.5	ĺ	(manative mana) manatah and (ank mana) mada manatah (and 100)	DERWENT	 00000000000000000000000000000000000
65	3	(passive near3 resonator) and (self near3 mode near3 lock\$3)	USPAT;	2003/07/27 14:36
			US-PGPUB;	
	İ		EPO; JPO;	
cc	240	(aalf paar) mada paar) laakt?)	DERWENT	2003/07/27 14:36
66	248	(self near3 mode near3 lock\$3)	USPAT; US-PGPUB;	2003/07/27 14.30
İ				
	·		EPO; JPO; DERWENT	
67	69	((solf near) made near) leak(\$2)) and least near diade	USPAT;	2003/07/27 14:37
67	69	((self near3 mode near3 lock\$3)) and laser near diode	US-PGPUB;	2003/07/27 14.37
			EPO; JPO;	
İ	i		DERWENT	
68	1	(((self near3 mode near3 lock\$3)) and laser near diode) and	USPAT;	2003/07/27 14:38
00	1	perturbation and (misalign\$4 or realign\$4)	US-PGPUB;	2000/01/21 14.00
	1	porturbation and (mindingriff to rodingriff t)	EPO; JPO;	
			DERWENT	
69	23	(((self near3 mode near3 lock\$3)) and laser near diode) and	USPAT;	2003/07/27 14:38
**		(perturbation or misalign\$4 or realign\$4)	US-PGPUB:	
		(F	EPO; JPO;	
			DERWENT	
_	2609	semiconductor near laser near diode	USPAT;	2003/07/27 12:53
			US-PGPUB	
-	2084	semiconductor adj laser adj diode	USPAT;	2002/10/19 18:17
			US-PGPUB	
-	95	(semiconductor adj laser adj diode) and mode near lock\$3	USPAT;	2002/10/19 18:18
			US-PGPUB	
-	51	((semiconductor adj laser adj diode) and mode near lock\$3) and	USPAT;	2002/10/19 18:18
		passive\$3	US-PGPUB	
-	20	((semiconductor adj laser adj diode) and mode near lock\$3) and	USPAT;	2002/10/19 18:19
		passive\$3 near mode near lock\$3	US-PGPUB	000040404040
-	20	(semiconductor adj laser adj diode) and (passive\$3 near mode	USPAT;	2002/10/19 18:19
	100	near lock\$3)	US-PGPUB	2002/40/40 40:44
-	160	(counterpropagating near (waves or pulses))	USPAT;	2002/10/19 18:41
	10	//counterpropagating pear (wayon or suless))) and (nearly-62	US-PGPUB	2002/40/40 49:47
-	10	((counterpropagating near (waves or pulses))) and (passive\$3	USPAT;	2002/10/19 18:47
1_	4	near mode near lock\$3) (((counterpropagating near (waves or pulses))) and (passive\$3	US-PGPUB USPAT;	2002/10/19 18:44
1 -	' '	near mode near lock\$3)) and (semiconductor near laser near	US-PGPUB	2002/10/18 10.44
	1	diode)	US-FGFUB	
1_	5	(((counterpropagating near (waves or pulses))) and (passive\$3	USPAT;	2002/10/19 18:44
_	3	near mode near lock\$3)) and (laser near diode)	US-PGPUB	2002/10/13 10:44
	130	(laser near diode) and (passive\$3 near mode near lock\$3)	USPAT:	2002/10/19 18:56
-	130	ן מאטין וופמו מוטעפן מווע (מאטין וופמו וווטער וופמו ווטער וופמו ווטער וופמו ווטער וופמו ווטער וופמו ווטער	US-PGPUB	2002/10/19 10:00
-	49	((laser near diode) and (passive\$3 near mode near lock\$3)) not	USPAT;	2002/10/19 18:49
1		(saturable adj absorber)	US-PGPUB	2002/10/10 10.79
<u> </u>		1 1	100,00	L

-	16	(((laser near diode) and (passive\$3 near mode near lock\$3)) not	USPAT;	2002/10/19 18:50
		(saturable adj absorber)) and (align\$4 or misalign\$4)	US-PGPUB	
-	10	misalign\$4 and (passive\$3 near mode near lock\$3)	USPAT;	2002/10/19 18:56
			US-PGPUB	
-	l 0	misalign\$4 near (passive\$3 near mode near lock\$3)	USPAT;	2002/10/19 19:00
	-	,	US-PGPUB	
-	76	self near mode near lock\$3	USPAT:	2002/10/19 19:30
			US-PGPUB	
-	l 0	((self near mode near lock\$3) and (laser near diode)) and	USPAT:	2002/10/19 19:02
		realign\$4	US-PGPUB	
	5	((self near mode near lock\$3) and (laser near diode)) and	USPAT:	2002/10/19 19:02
-		misalign\$4	US-PGPUB	2002, 10, 10 10,02
_	25	(self near mode near lock\$3) and (laser near diode)	USPAT;	2002/10/19 19:06
-	23	(sell fleat filode fleat lockys) and (laser fleat diode)	US-PGPUB	2002/10/10 10:00
	18	((self near mode near lock\$3) and (laser near diode)) not	USPAT;	2002/10/19 19:30
-	10	(saturable adj absorber)	US-PGPUB	2002/10/13 13.50
	5	(self near mode near lock\$3) and ring near cavity	USPAT;	2002/10/19 19:31
•]	(Sell fleat fliode fleat lock\$5) and fling fleat cavity	US-PGPUB	2002/10/19 19.51
	185	(laser near diode) and (ring near cavity)	USPAT;	2002/10/19 19:32
-	100	(laser flear glode) and (fing flear cavity)	US-PGPUB	2002/10/19 19.32
	60	(/languages diado) and (ring magraphity)) and (made near leak\$2)	USPAT:	2002/10/19 19:39
-	62	((laser near diode) and (ring near cavity)) and (mode near lock\$3)		2002/10/19 19.39
	0.7	100	US-PGPUB	2002/40/40 40-22
-	37		USPAT;	2002/10/19 19:33
		lock\$3)) and (self or passive\$3)	US-PGPUB	2002/40/40 40:22
-	22		USPAT;	2002/10/19 19:33
	_	lock\$3)) and (self or passive\$3)) not (saturable adj absorber)	US-PGPUB	0000/40/40 40:45
-	1	((laser near diode) and (ring near cavity)) and (self near mode	USPAT;	2002/10/19 19:45
	0004	near lock\$3)	US-PGPUB	2002/40/40 40:46
-	2084	semiconductor adj laser adj diode	USPAT;	2002/10/19 19:46
	1	/	US-PGPUB	0000/40/40 40-54
-	18	(semiconductor adj laser adj diode) and 372/94.ccls.	USPAT;	2002/10/19 19:51
	l .		US-PGPUB	00004040404040
-	1	((semiconductor adj laser adj diode) and 372/94.ccls.) and	USPAT;	2002/10/19 19:48
		(passive\$3 near mode near lock\$3)	US-PGPUB	
-	0	, ((USPAT;	2002/10/19 19:48
	_	near mode near lock\$3)	US-PGPUB	000040404040
-	6	((semiconductor adj laser adj diode) and 372/94.ccls.) and (mode	USPAT;	2002/10/19 19:48
		near lock\$3)	US-PGPUB	
-	99	laser adj diode and 372/94.ccls.	USPAT;	2002/10/19 19:52
			US-PGPUB	
-	1	(laser adj diode and 372/94.ccls.) and self adj mode adj locking	USPAT;	2002/10/19 19:52
			US-PGPUB	
-	6	(laser adj diode and 372/94.ccls.) and passive adj mode adj	USPAT;	2002/10/19 19:55
		locking	US-PGPUB	
-	50	(semiconductor adj laser adj diode) and ((ring near cavity) or (ring	USPAT;	2002/10/19 19:56
	1	near laser))	US-PGPUB	
-	1	((semiconductor adj laser adj diode) and ((ring near cavity) or	USPAT;	2002/10/19 19:57
		(ring near laser))) and ((self adj mode adj lock\$3) or (passive adj	US-PGPUB	
		mode adj lock\$3))		